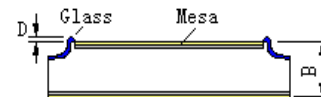
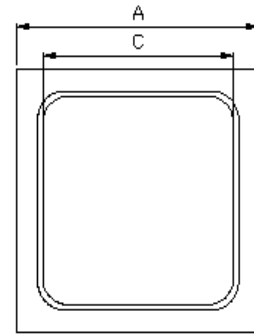


Features

- Glass passivated chip
- Low forward voltage drop
- High current capability
- High reliability
- High surge current capability
- Surface Metalization: Ni(0.6~1um)/Au(0.05um)
- Compatible with soldering
- Operating Junction temperature range :-55 ~ +150°C
- High Efficiency/Ultra Fast Recovery Rectifier



Process Details

Chip Part No.	Chip size	PDPW (pcs/4"wafer)	Size (mil)			
			A (+1/-2)	B (±1)	C (±2)	D (±0.5)
GDGH50A-M	50*50mil	4,469	50	10	31	1
GDGH56A-M	56*56mil	3,685	56	10	36	1
GDGH60A-M	60*60mil	3,011	60	10	37	1
GDGH95A-M	95*95mil	1,153	95	10	69	1
GDGH140A-M	140*140mil	521	140	10	114	1

Maximum Ratings

(TA = 25 °C unless otherwise noted)

Parameter	Symbol	VALUE							UNIT
		A	B	D	G	J	K	M	
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified current	$I_{F(AV)}$	See Next Table							A
Maximum instantaneous forward voltage at IF	V_F	See Next Table							V
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I_{FSM}	See Next Table							A

Representative Parameter

Chip size/mil	$I_F(A)$	$V_F(V)@I_F$	$V_{BL}(V)@I_1=10\mu A$	$I_R(\mu A)@V_R$	T_{RR}/ns
50	1	1.3	50~400	1	<50
56	1.5	1.3	50~400	1	<50
60	2	1.3	50~400	1	<50
95	3	1.3	50~400	1	<50
140	6	1.3	50~400	1	<50

Chip size/mil	$I_F(A)$	$V_F(V)@I_F$	$V_{BL}(V)@I_1=10\mu A$	$I_R(\mu A)@V_R$	T_{RR}/ns
50	1	1.7	600~1000	1	<75
56	1.5	1.7	600~1000	1	<75
60	2	1.7	600~1000	1	<75
95	3	1.7	600~1000	1	<75
140	6	1.7	600~1000	1	<75